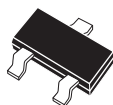


**2N7002**  
**N-CHANNEL**  
**ENHANCEMENT-MODE**  
**MOSFET**



**SOT-23 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N7002 type is a N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications.

**MARKING CODE: 702**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

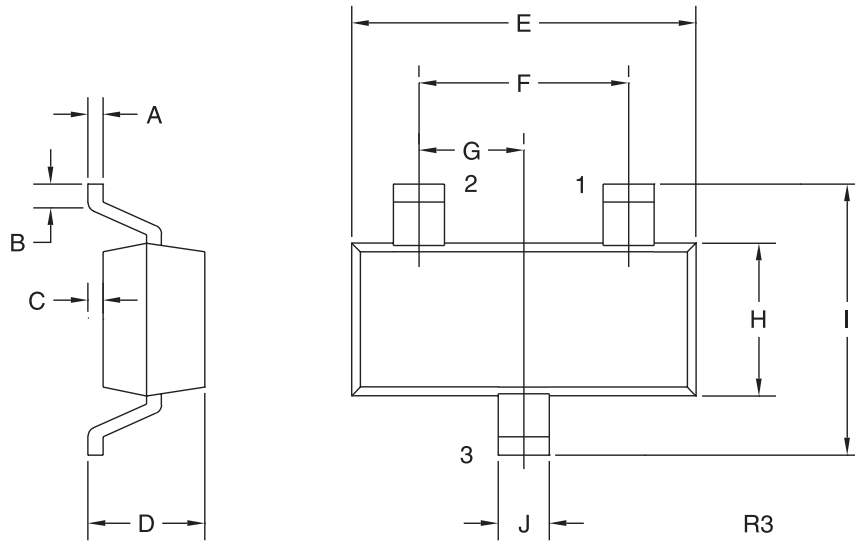
	SYMBOL		UNITS
Drain-Source Voltage	$V_{DS}$	60	V
Drain-Gate Voltage	$V_{DG}$	60	V
Gate-Source Voltage	$V_{GS}$	40	V
Continuous Drain Current ( $T_C=25^\circ\text{C}$ )	$I_D$	115	mA
Continuous Drain Current ( $T_C=100^\circ\text{C}$ )	$I_D$	75	mA
Continuous Source Current (Body Diode)	$I_S$	115	mA
Maximum Pulsed Drain Current	$I_{DM}$	800	mA
Maximum Pulsed Source Current	$I_{SM}$	800	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{GSSF}$	$V_{GS}=20\text{V}$			100	nA
$I_{GSSR}$	$V_{GS}=20\text{V}$			100	nA
$I_{DSS}$	$V_{DS}=60\text{V}, V_{GS}=0$			1.0	$\mu\text{A}$
$I_{DSS}$	$V_{DS}=60\text{V}, V_{GS}=0, T_A=125^\circ\text{C}$			500	$\mu\text{A}$
$I_{D(ON)}$	$V_{DS} \geq 2V_{DS(ON)}, V_{GS}=10\text{V}$	500			mA
$BV_{DSS}$	$I_D=10\mu\text{A}$	60	105		V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	2.1	2.5	V
$V_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$			3.75	V
$V_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$			1.5	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		3.7	7.5	$\Omega$
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}, T_A=100^\circ\text{C}$			13.5	$\Omega$
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		6.2	7.5	$\Omega$
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}, T_A=100^\circ\text{C}$			13.5	$\Omega$
gFS	$V_{DS} \geq 2V_{DS(ON)}, I_D=200\text{mA}$	80			mmhos
$C_{rss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			5.0	pF
$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			50	pF
$C_{oss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			25	pF
$t_{on}$	$V_{DD}=30\text{V}, I_D=10\text{V}, R_G=25\Omega, R_L=25\Omega$			20	ns
$t_{off}$	$V_{DD}=30\text{V}, I_D=10\text{V}, R_G=25\Omega, R_L=25\Omega$			20	ns
$V_{SD}$	$V_{GS}=0\text{V}, I_S=11.5\text{mA}$			1.5	V

R3 (26-September 2002)

SOT-23 CASE - MECHANICAL OUTLINE



**LEAD CODE:**

- 1) GATE
- 2) SOURCE
- 3) DRAIN

**MARKING CODE: 702**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)